

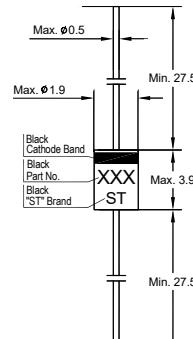
# 1N4148

## Silicon Epitaxial Planar Switching Diode

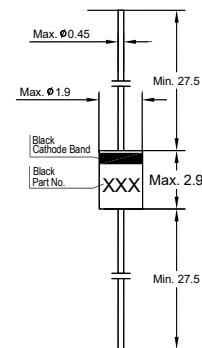
### Applications

- High-speed switching

This diode is also available in MiniMELF case with the type designation LL4148



Glass Case DO-35  
Dimensions in mm



Glass Case DO-34  
Dimensions in mm

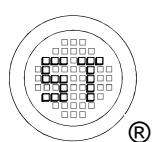
### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter  | Symbol      | Value         | Unit |
|--|-------------|---------------|------|
| Peak Reverse Voltage   | $V_{RM}$    | 100           | V    |
| Reverse Voltage  | $V_R$       | 75            | V    |
| Average Rectified Forward Current  | $I_{F(AV)}$ | 200           | mA   |
| Non-repetitive Peak Forward Surge Current<br>at $t = 1 \text{ s}$<br>at $t = 1 \text{ ms}$<br>at $t = 1 \mu\text{s}$ | $I_{FSM}$   | 0.5<br>1<br>4 | A    |
| Power Dissipation  | $P_{tot}$   | 500           | mW   |
| Operating Junction Temperature Range   | $T_j$       | - 65 to + 200 | °C   |
| Storage Temperature Range  | $T_{stg}$   | - 65 to + 200 | °C   |

### Thermal Characteristics

| Parameter   | Symbol          | Max. | Unit |
|---|-----------------|------|------|
| Thermal Resistance - Junction to Lead <sup>1)</sup> | $R_{\theta JL}$ | 350  | °C/W |

<sup>1)</sup> Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

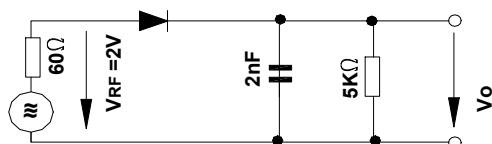


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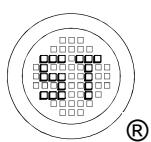
## Characteristics at $T_a = 25^\circ\text{C}$

| Parameter  | Symbol                                   | Min.        | Max.          | Unit                                 |
|--|--|-------------|---------------|--------------------------------------|
| Reverse Breakdown Voltage<br>at $I_R = 100 \mu\text{A}$<br>at $I_R = 5 \mu\text{A}$  | $V_{(\text{BR})R}$<br>$V_{(\text{BR})R}$ | 100<br>75   | -<br>-        | V<br>V                               |
| Forward Voltage<br>at $I_F = 10 \text{ mA}$  | $V_F$                                    | -           | 1             | V                                    |
| Leakage Current<br>at $V_R = 20 \text{ V}$<br>at $V_R = 75 \text{ V}$<br>at $V_R = 20 \text{ V}, T_j = 150^\circ\text{C}$                              | $I_R$<br>$I_R$<br>$I_R$                  | -<br>-<br>- | 25<br>5<br>50 | nA<br>$\mu\text{A}$<br>$\mu\text{A}$ |
| Capacitance<br>at $V_R = 0, f = 1 \text{ MHz}$   | $C_{\text{tot}}$                         | -           | 4             | pF                                   |
| Voltage Rise when Switching ON<br>tested with 50 mA Forward Pulses<br>$t_p = 0.1 \text{ s}$ , Rise Time < 30 ns, $f_p = 5 \text{ to } 100 \text{ KHz}$ | $V_{\text{fr}}$                          | -           | 2.5           | V                                    |
| Reverse Recovery Time<br>at $I_F = 10 \text{ mA}, I_{rr} = 1 \text{ mA}, V_R = 6 \text{ V}, R_L = 100 \Omega$  | $t_{rr}$                                 | -           | 4             | ns                                   |
| Rectification Efficiency <sup>1)</sup><br>at $f = 100 \text{ MHz}, V_{RF} = 2 \text{ V}$   | $\eta_V$                                 | 0.45        | -             | -                                    |

1)



Rectification Efficiency Measurement Circuit



## Electrical Characteristics Curve

Fig 1. Power Derating Curve

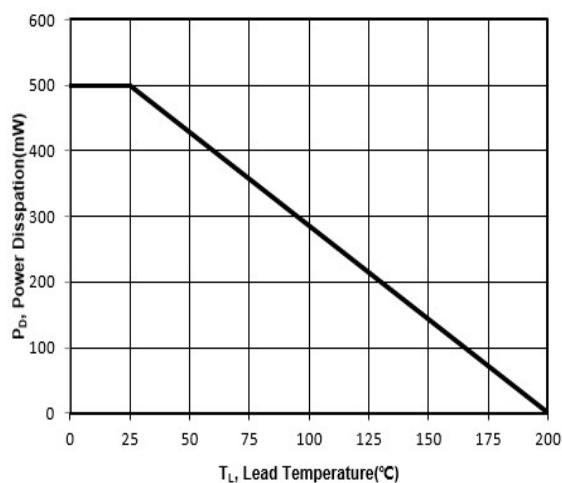


Fig 2. Forward Characteristic Curve

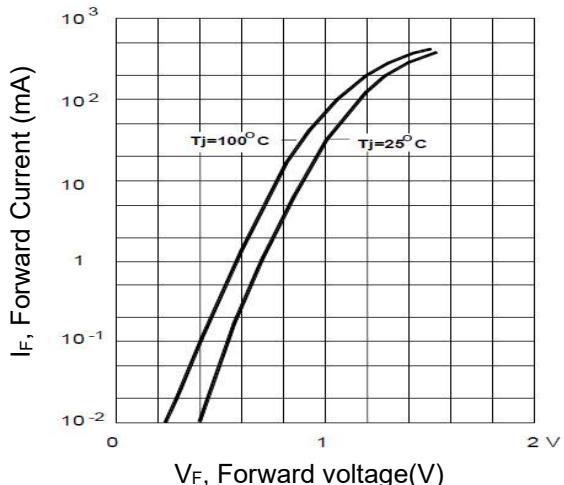


Fig 3. Reverse Characteristic Curve

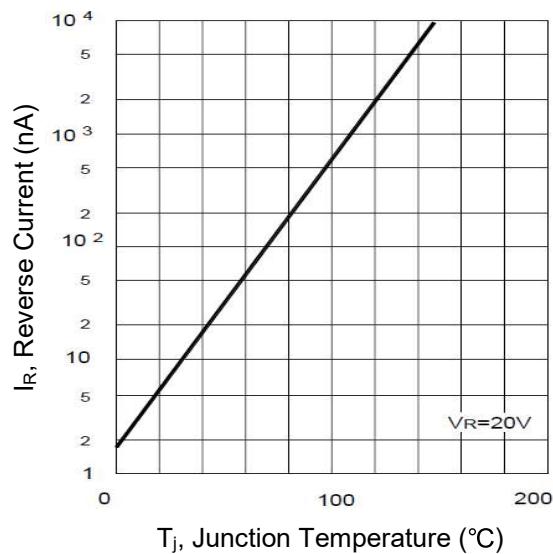


Fig 4. Junction Capacitance

